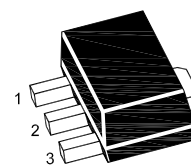


MCR100...U Series

Sensitive Gate Silicon Controlled Rectifiers Reverse Blocking Thyristors



1.Gate 2.Anode 3.Cathode
SOT-89 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Repetitive Off-State Voltage ⁴⁾ ($T_J = -40^\circ\text{C}$ to 110°C , Sine Wave, 50 to 60 Hz, Gate Open) MCR100-4U MCR100-6U MCR100-8U	V_{DRM}, V_{RRM}	200 400 600	V
On-State RMS Current ($T_C = 80^\circ\text{C}$) 180° Conduction Angles	$I_{T(RMS)}$	0.8	A
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, $T_J = 25^\circ\text{C}$)	I_{TSM}	10	A
Circuit Fusing Considerations ($t = 8.3$ ms)	I^2t	0.415	A^2s
Forward Peak Gate Power (Pulse Width ≤ 1 μs)	P_{GM}	0.1	W
Forward Average Gate Power ($t = 8.3$ ms)	$P_{G(AV)}$	0.1	W
Peak Gate Current – Forward (Pulse Width ≤ 1 μs)	I_{GM}	1	A
Peak Gate Voltage – Reverse (Pulse Width ≤ 1 μs)	V_{GRM}	5	V
Operating Junction Temperature Range	T_J	- 40 to + 110	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 40 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

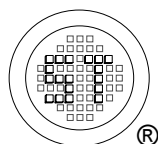
Parameter	Symbol	Max.	Unit
Peak Forward or Reverse Blocking Current ²⁾ at $V_D = \text{Rated } V_{DRM} \text{ and } V_{RRM}, R_{GK} = 1 \text{ K}\Omega$	I_{DRM}, I_{RRM}	10	μA
Peak Forward On-State Voltage ¹⁾ at $I_{TM} = 1 \text{ A Peak}$	V_{TM}	1.7	V
Gate Trigger Current ³⁾ at $V_{AK} = 7 \text{ V}, R_L = 100 \Omega$	I_{GT}	200	μA
Holding Current ²⁾ at $V_{AK} = 7 \text{ V}, \text{Initiating Current} = 20 \text{ mA}$	I_H	$T_C = 25^\circ\text{C}$: 5 $T_C = -40^\circ\text{C}$: 10	mA
Latch Current at $V_{AK} = 7 \text{ V}, I_g = 200 \mu\text{A}$	I_L	$T_C = 25^\circ\text{C}$: 10 $T_C = -40^\circ\text{C}$: 15	mA
Gate Trigger Voltage ³⁾ at $V_{AK} = 7 \text{ V}, R_L = 100 \Omega$	V_{GT}	$T_C = 25^\circ\text{C}$: 0.8 $T_C = -40^\circ\text{C}$: 1.2	V

¹⁾ Indicates pulse test width ≤ 1 ms, duty cycle $\leq 1\%$

²⁾ $R_{GK} = 1 \text{ K}\Omega$ included in measurement

³⁾ Does not include R_{GK} in measurement

⁴⁾ V_{DRM} and V_{RRM} for all types can be applied on continuous basis. Ratings apply for zero negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



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ISO/TS 16949 : 2009
Certificate No. 160713009

ISO 14001 : 2004
Certificate No. 7116

ISO 9001 : 2008
Certificate No. 0719410

BS-OHSAS 18001 : 2007
Certificate No. 7116

IECQ QC 080000
Certificate No. PRC/HS/4-165-1

MCR100...U Series

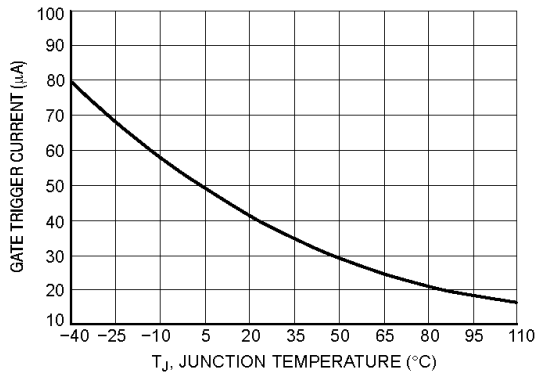


Figure 1. Typical Gate Trigger Current versus Junction Temperature

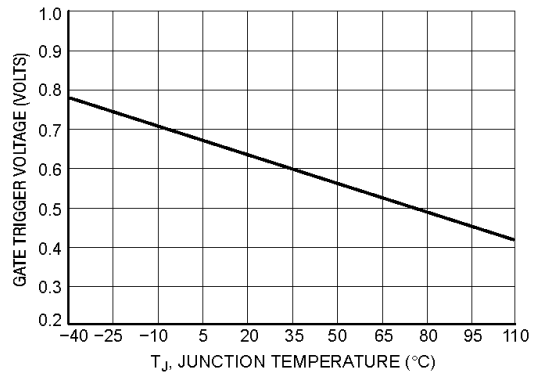


Figure 2. Typical Gate Trigger Voltage versus Junction Temperature

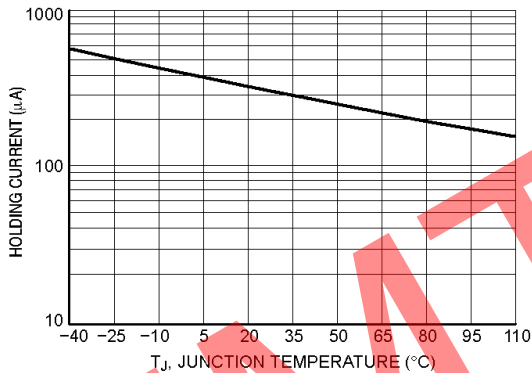


Figure 3. Typical Holding Current versus Junction Temperature

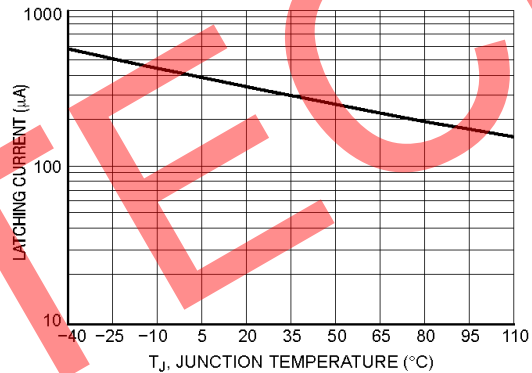


Figure 4. Typical Latching Current versus Junction Temperature

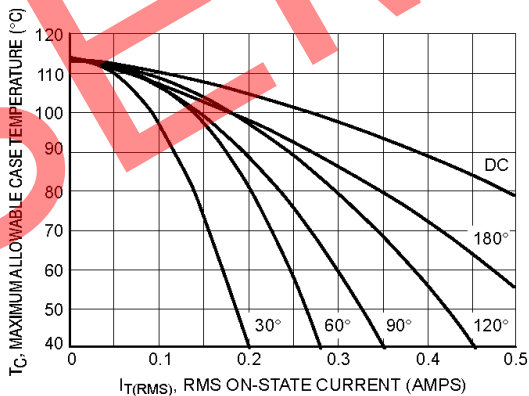


Figure 5. Typical RMS Current Derating

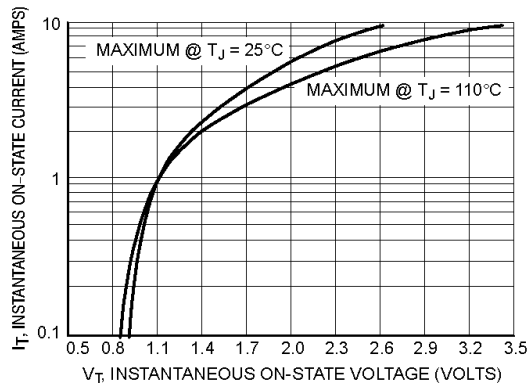
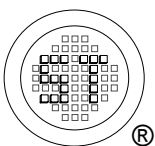


Figure 6. Typical On-State Characteristics

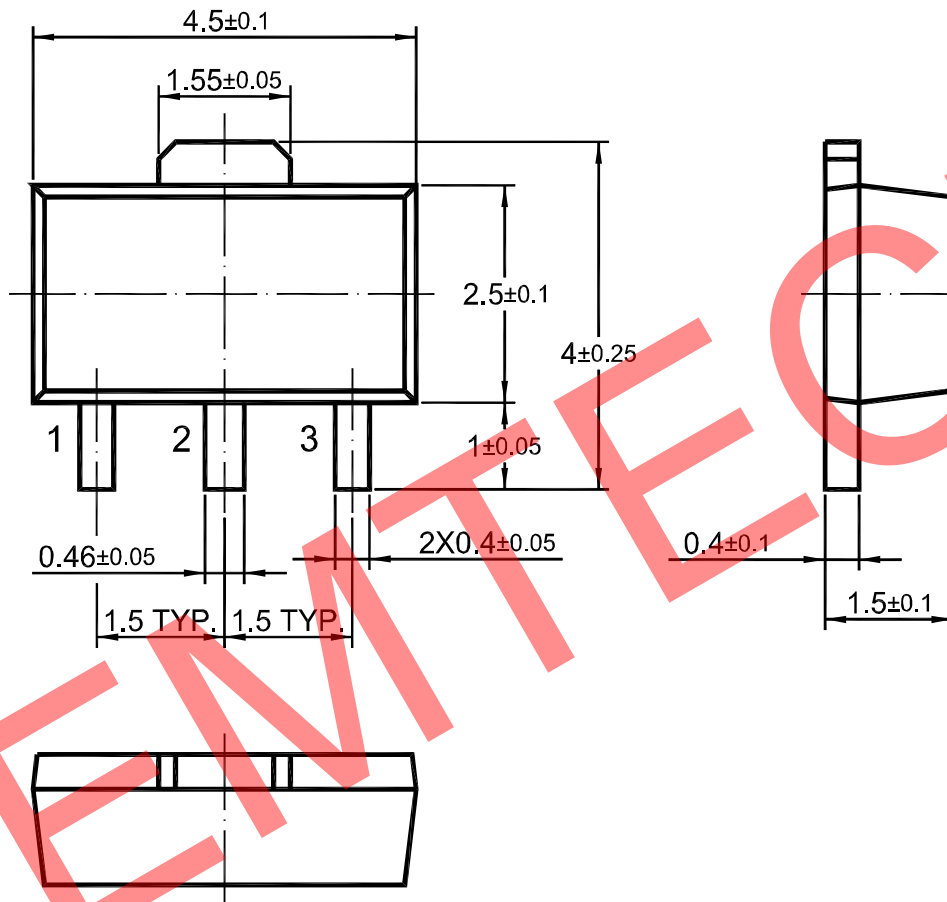


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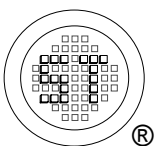


MCR100...U Series

SOT-89 PACKAGE OUTLINE



Dimensions in mm



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Certificate No. PRC-HSPH-185-1

Dated: 27/12/2013 Rev: 01